

Silicon NPN transistor epitaxial type CP898

[Applications]

Industrial and consumer high speed switch required products
Medium power amplifier

[Feature]

Electrical characteristics equivalent with MMBT4401
High level emitter-base voltage BVEBO= 8V

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	60	V
Collector-emitter voltage	VCEO	40	V
Emitter-base voltage	VEBO	8	V
Collector current	IC	600	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	60	-	-	V	IC= 100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	40	-	-	V	IC= 1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	8	-	-	V	IE= 100uA, IC= 0A
Collector cut-off current	ICEX	-	-	100	nA	VCE= 35V, VEB= 0.4V
Emitter cut-off current	IEBO	-	-	100	nA	VEB= 6V, IC= 0A
DC current gain 1	hFE 1	20	-	-	-	VCE= 1V, IC= 0.1mA
DC current gain 2	hFE 2	40	-	-	-	VCE= 1V, IC= 1mA
DC current gain 3	hFE 3	80	-	-	-	VCE= 1V, IC= 10mA
DC current gain 4	hFE 4	100	-	300	-	VCE= 1V, IC= 150mA
DC current gain 5	hFE 5	40	-	-	-	VCE= 2V, IC= 500mA
Collector-emitter saturation voltage 1	VCE(sat) 1	-	-	0.4	V	IC= 150mA, IB= 15mA
Collector-emitter saturation voltage 2	VCE(sat) 2	-	-	0.75	V	IC= 500mA, IB= 50mA
Base-emitter saturation voltage 1	VBE(sat) 1	0.75	-	0.95	V	IC= 150mA, IB= 15mA
Base-emitter saturation voltage 2	VBE(sat) 2	-	-	1.2	V	IC= 500mA, IB= 50mA
Transition frequency	f T	250	-	-	MHz	VCE= 10V, IE= -20mA
Output capacitance	Cob	-	-	6.5	pF	VCB= 5V, f = 1MHz, IE= 0A
Input capacitance	Cib	-	-	30	pF	VEB= 0.5V, f = 1MHz, IE= 0A
Delay Time	td	-	-	15	ns	VCC= 30V, VBE= -2V
Rise Time	tr	-	-	20	ns	IC= 150mA, IB1= 15mA
Storage Time	tstg	-	-	225	ns	VCC= 30V, IC= 150mA
Fall Time	tf	-	-	30	ns	IB1= -IB2= 15mA

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 hFE - IC
at Ta= 25C

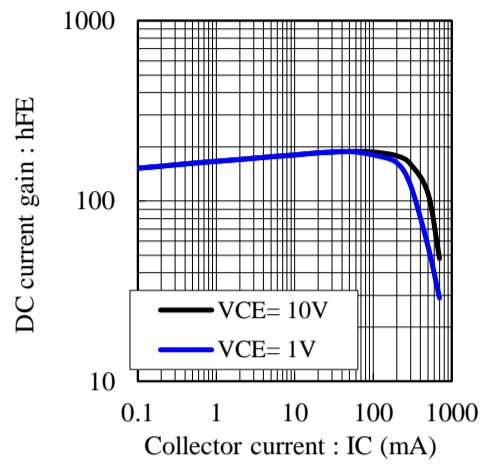


Fig.2 VCE(sat) - IC
at IC/IB= 10, Ta= 25C

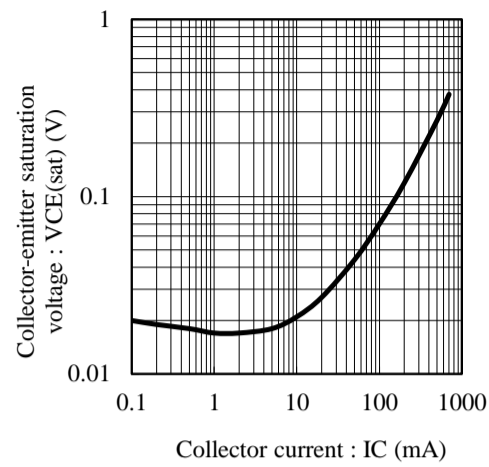


Fig.3 VBE(sat) - IC
at IC/IB= 10, Ta= 25C

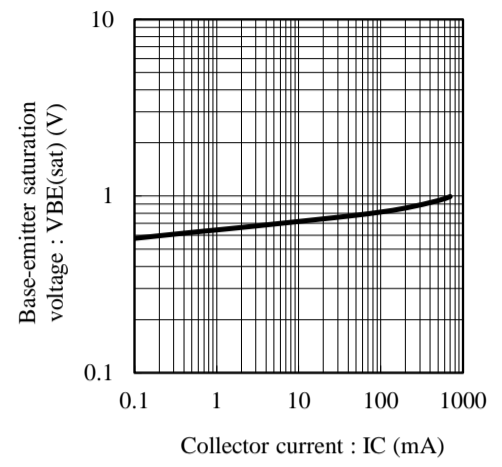


Fig.4 fT - IE
at VCE= 20V, Ta= 25C

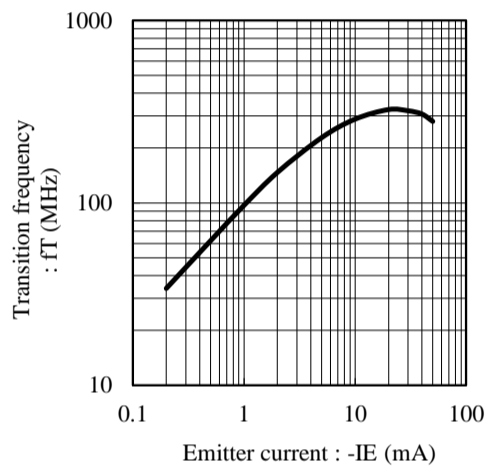


Fig.5 Cob - VCB
at f= 1MHz, Ta= 25C

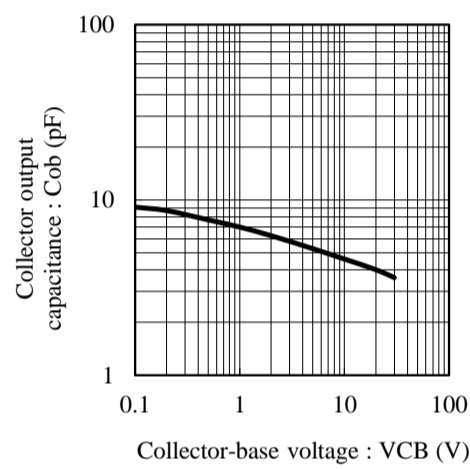


Fig.6 Cib - VEB
at f= 1MHz, Ta= 25C

